

Justify your answers, use only standard symbols. **TOTAL 3 Questions**

NOTE:

- ✓ Symbols have their usual meaning. Answers should be clear, concise and legible. Specify your assumptions clearly.
- ✓ **No marks** for unnecessary theoretical explanations. Marks will be deducted for calculation mistakes.
- ✓ Take $\gamma = \lambda = 0$ (for 0.5 micron technology, assume long channel MOSFET equations are valid)

$V_{DD} = 3.3 \text{ V}, L_{min} = 1 \mu\text{m}$

NMOS --- $V_{TN} = 0.7 \text{ V} \quad \gamma = 0.45 \sqrt{\text{V}} \quad K' = \mu_n C_{OX} = 140 \mu\text{A}/\text{V}^2 \quad \lambda = 0.1 \text{ V}^{-1}$

PMOS ---- $V_{TP} = -0.7 \text{ V} \quad \gamma = 0.4 \sqrt{\text{V}} \quad K' = \mu_p C_{OX} = 40 \mu\text{A}/\text{V}^2 \quad \lambda = 0.1 \text{ V}^{-1}$

Unless necessarily required or specified in the question.

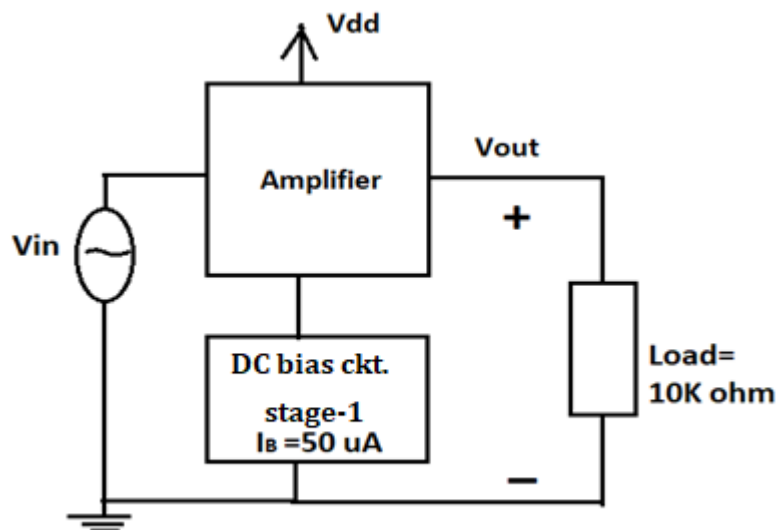
-assume $\gamma = \lambda = 0$ in drain current analysis. Bulk terminal of all NMOS/ PMOS connected to ground/ V_{DD} **Assume matching of devices and operating in saturation region wherever required**

Q1. Consider the block level diagram of a 2 stage amplifier with active load circuit shown in **Fig. 1**.

Given = DC current I_B (of stage-1) = 50 μA . $V_{in} = 1.5 \text{ V} + 5 \text{ mV} \sin \omega t$, $V_{ov} = 0.2 \text{ V}$, $V_{out} \text{ (DC)} = 0.7 \text{ V}$

Required dynamic specifications of amplifier --- $R_{in} > 100 \text{ M}\Omega$, $R_{out} \leq 1 \text{ K}\Omega$, $|A_{vo}| = (v_{out}/v_{in}) \geq 100$,

- a) Based on data given, write the name of stage-1 and stage-2 of the given amplifier .
- b) Sketch and label the complete schematic of the entire circuit. Clearly mark stage-1 and stage-2 in you diagram. Also specify matched transistor pair/s.



- c) Determine the value of bias current of second stage of amplifier.
- d) Write values of DC voltages at every node in circuit of part (b)
- e) Determine the value of A_v (with load) = (v_{out}/v_{in})

[10]

Q2. Consider the circuit shown in Fig. 2 .

Given $V_{OV} = 0.2V$. Assume matching of differential arms in the circuit. .

I_{SS} (basic current mirror circuit) = $100 \mu A = 2 I_{D,5,6}$

$V_{id} = v_{in1} - v_{in2} = 10 \text{ mV} \sin \omega t + 1.7V$,

$V_{od} = v_{out1} - V_{out2}$

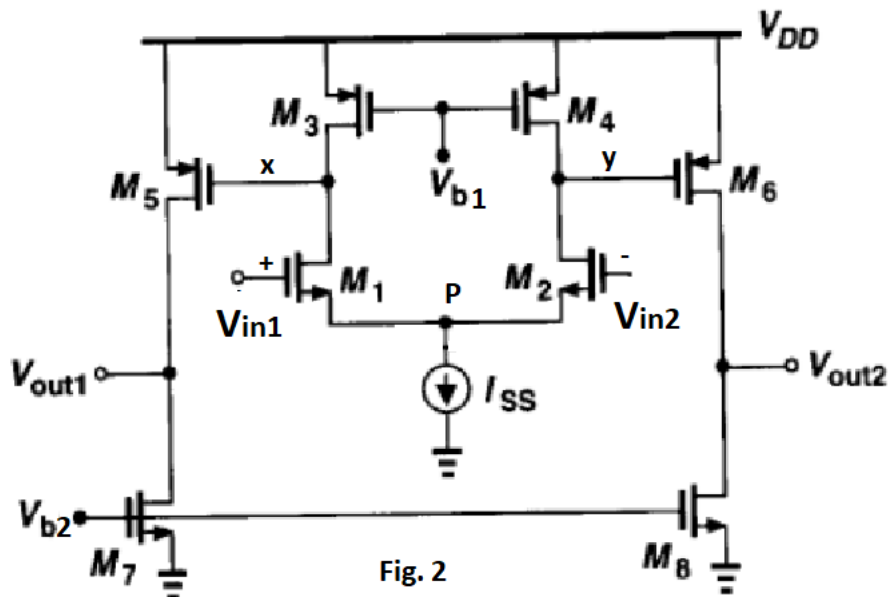


Fig. 2

- a) Identify the type of amplifier in Fig. 2
- b) Determine small signal voltage gain $A_{dm} = \left(\frac{v_{od}}{v_{id}} \right)$ in dB
- c) Modify the following equation , in case of mismatch in differential arms , in terms of differential input only.
Given Input $v_{in1} = v_{in2} = v_{icm}$ remains equal.

$$v_{od} = A_{dm} v_{id} + A_{cm} v_{icm}$$

- d) If trans-conductance of only M5 and M6 transistors get 2 % mismatch during fabrication such that $|g_{m5}| \neq |g_{m6}|$. Determine the value of $g_{m, \text{nominal}}$ and Δg_m
- e) For **part (d)**, calculate the value of $|v_{od}|$ due to mismatch . Here, assume $r_{o5} = r_{o6}$ in calculations.

Hence calculate $|A_{cm}|_{\text{diff}}$ in part (d). Given Input $v_{in1} = v_{in2} = v_{icm}$ remains same.

[12]

Q3. Answer the following. Justify with reason/s .

- a) The intrinsic gain of a MOSFET does not change with change in bias current. Why?
- b) Source degeneration of a MOSFET increases its dynamic resistance. Why?
- c) In cascode amplifier, cascode transistor is replaced by a passive resistor R. Write the voltage gain expression intuitively.
- d) What is the significance of figure of merit $\{g_m / I_D\}$ of MOSFET amplifier

[5]

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